

HCF4052B

DIFFERENT 4-CHANNEL ANALOG MULTIPLEXER/DEMULTIPLEXER

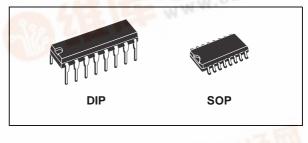
- LOW "ON" RESISTANCE : 125Ω (Typ.) OVER 15V p.p SIGNAL-INPUT RANGE FOR $V_{DD} - V_{EE} = 15V$
- HIGH "OFF" RESISTANCE : CHANNEL LEAKAGE \pm 100pA (Typ.) at $V_{DD} - V_{EE} = 18V$
- BINARY ADDRESS DECODING ON CHIP
- **HIGH DEGREE OF LINEARITY: < 0.5%** DISTORTION TYP. at $f_{IS} = 1 \text{KHz}$, $V_{IS} = 5 V_{pp}$, $V_{DD} - V_{SS} \ge 10V$, RL = $10K\Omega$
- VERY LOW QUIESCENT POWER DISSIPATION UNDER ALL DIGITAL CONTROL INPUT AND SUPPLY CONDITIONS: 0.2 µW (Typ.) at V_{DD} - $V_{SS} = V_{DD}$ - $V_{EE} = 10V$
- MATCHED SWITCH CHARACTERISTICS: $R_{ON} = 5\Omega$ (Typ.) FOR $V_{DD} - V_{EE} = 15V$
- WIDE RANGE OF DIGITAL AND ANALOG SIGNAL LEVELS: DIGITAL 3 to 20, ANALOG TO 20V p.p.
- QUIESCENT CURRENT SPECIF. UP TO 20V
- 5V, 10V AND 15V PARAMETRIC RATINGS
- INPUT LEAKAGE CURRENT $I_{I} = 100 \text{nA} \text{ (MAX) AT V}_{DD} = 18 \text{V T}_{A} = 25 ^{\circ}\text{C}$
- 100% TESTED FOR QUIESCENT CURRENT
- MEETS ALL REQUIREMENTS OF JEDEC JESD13B " STANDARD SPECIFICATIONS FOR DESCRIPTION OF B SERIES CMOS **DEVICES**"

DESCRIPTION

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The HCF4052B is a monolithic integrated circuit fabricated in Metal Oxide Semiconductor

PIN CONNECTION

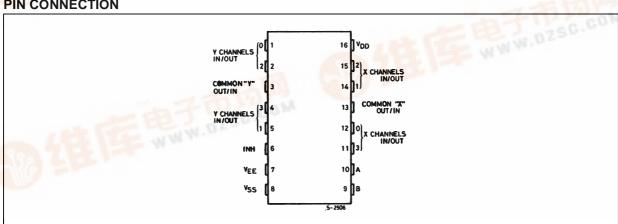


ORDER CODES

PACKAGE	TUBE	T&R
DIP	HCF4052BEY	N. All
SOP	HCF4052BM1	HCF4052M013TR

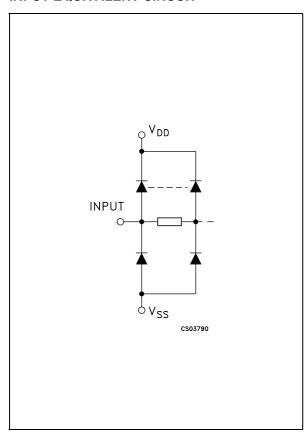
technology available in DIP and SOP packages. The HCF4052B analog multiplexer/demultiplexer is a digitally controlled analog switch having low ON impedance and very low OFF leakage current. This multiplexer circuit dissipate extremely low quiescent power over the full VDD - VSS and VDD -V_{FF} supply voltage range, independent of the logic state of the control signals.

When a logic "1" is present at the inhibit input terminal all channel are off. This device is a differential 4-channel multiplexer having two binary control inputs, A and B and an inhibit input. The two binary input signals selects 1 of 4 pairs of channels to be turned on and connect the analog inputs to the outputs.



October 2002 1/11

INPUT EQUIVALENT CIRCUIT



PIN DESCRIPTION

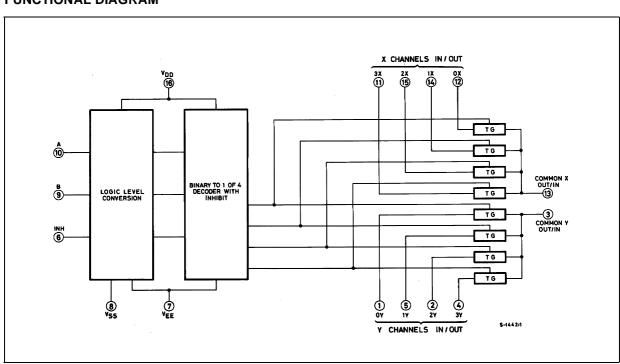
PIN No	SYMBOL	NAME AND FUNCTION
10, 9	A, B	Binary Control Inputs
6	INH	Inhibit Inputs
12, 14, 15, 11	0X to 3X CHANNEL IN/OUT	X channels Input/Output
1, 5, 2, 4	0Y to 3Y CHANNEL IN/OUT	Y channels Input/Output
3	COM Y OUT/ IN	Y Common Output/Input
13	COM X OUT/ IN	X Common Output/Input
7	V _{EE}	Supply Voltage
8	V_{SS}	Negative Supply Voltage
16	V_{DD}	Positive Supply Voltage

TRUTH TABLE

INHIBIT	В	Α	
0	0	0	0x, 0y
0	0	1	1x, 1y
0	1	0	2x, 2y 3x, 3y
0	1	1	3x, 3y
1	Х	Х	NONE

X : Don't Care

FUNCTIONAL DIAGRAM



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V_{DD}	Supply Voltage	-0.5 to +22	V
VI	DC Input Voltage	-0.5 to V _{DD} + 0.5	V
I _I	DC Input Current	± 10	mA
P _D	Power Dissipation per Package	500 (*)	mW
	Power Dissipation per Output Transistor	100	mW
T _{op}	Operating Temperature	-55 to +125	°C
T _{stg}	Storage Temperature	-65 to +150	°C

Absolute Maximum Ratings are those values beyond which damage to the device may occur. Functional operation under these conditions is not implied.

All voltage values are referred to V_{SS} pin voltage.

(*) 500mW at 65 °C; derate to 300mW by 10mW/°C from 65°C to 85°C

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Value	Unit
V_{DD}	Supply Voltage	3 to 20	V
V _I	Input Voltage	0 to V _{DD}	V
T _{op}	Operating Temperature	-55 to 125	°C

DC SPECIFICATIONS

		Test Condition				Value							
Symbol	Parameter	V _{IS}	V _{EE}	Vss	V _{DD}	Т	A = 25°	С	-40 to	85°C	-55 to	125°C	Unit
		(V)	(V)	(V)	(V)	Min.	Тур.	Max.	Min.	Max.	Min.	Max.	
ΙL	Quiescent Device				5		0.04	5		150		150	
	Current (all				10		0.04	10		300		300	μA
	switches ON or all switches OFF)				15		0.04	20		600		600	μΑ
	ownonce of 1)				20		0.08	100		3000		3000	
SWITCH													
R_{ON}	Resistance	0 <u><</u> V ₁ <u><</u>			5		470	1050		1200		1200	
		V _{DD}	0	0	10		180	400		520		520	Ω
		. 00			15		125	280		360		360	
Δ_{ON}	Resistance Δ_{RON}	0 <u><</u> V ₁ <u><</u>			5		10						
	(between any 2 of	V _{DD}	0	0	10		10						Ω
	4 switches)	, DD			15		5						
OFF*	Channel Leakage Current (All Channel OFF) (COMMON O/I)		0	0	18		±0.1	100		1000		1000	nA
OFF*	Channel Leakage Current (Any Channel OFF)		0	0	18		±0.1	100		1000		1000	nA
C _I	Input Capacitance						5						
Co	Output Capacitance		-5	-5	5		18						pF
C _{IO}	Feed through						0.2						
CONTRO	DL (Address or Inhi	bit)		I	I	I		I	I		I	•	
V _{IL}	Input Low Voltage		V _{EE} =	= Voo	5			1.5		1.5		1.5	
				1KΩ	10			3		3		3	V
		= VDD	to \		15			4		4		4	
V _{IH}	Input High Voltage	thru 1KΩ		2μΑ	5	3.5	İ		3.5	İ	3.5		
		11142	(on al	I OFF	10	7			7		7		V
			chan	nels)	15	11			11		11		
I _{IH,} I _{IL}	Input Leakage Current	VI	= 0/18\	/	18		±10 ⁻³	±0.1		±1		±1	μΑ
C _I	Input Capacitance						5	7.5					рF

^{*} Determined by minimum feasible leakage measurement for automating testing.

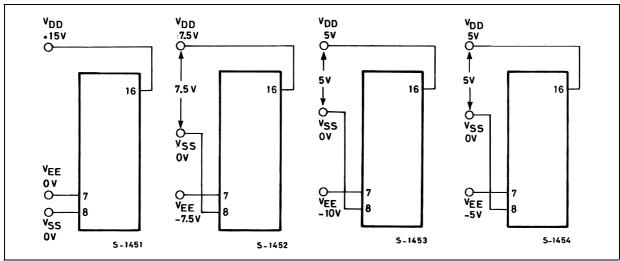
DYNAMIC ELECTRICAL CHARACTERISTICS ($T_{amb} = 25^{\circ}C$, $C_{L} = 50 pF$, all input square wave rise and fall time = 20 ns)

				Test Co	ndition				Value		Unit
Parameter	V _{EE} (V)	R _L (ΚΩ)	f _I (KHz)	V _I (V)	V _{SS} (V)	V _{DD} (V)		Min.	Тур.	Max.	
Propagation Delay				V_{DD}		5			30	60	
Time (signal input to		200		V DD		10			15	30	ns
output)						15			11	20	
Frequency Response Channel "ON" (sine	= V _{SS}	1		5(*)		10	V _O at Common OUT/IN		25		MHz
wave input) at 20 log V _O /V _I = - 3dB	- * 55	,		3()		10	V _O at any channel		60		IVII IZ
Feed through (all channels OFF) at 20 log V _O /V _I = - 40dB	= V _{SS}	1		5(*)		10	V _O at Common OUT/IN		10		MHz
20 log V _O /V _I = - 400B	50	,		3()		10	V _O at any channel		8		1011 12
Frequency Signal Crosstalk at	= V _{SS}	1		5(*)		10	Between Sections (measured on common)		6		MHz
$20 \log V_{O}/V_{I} = -40 dB$	- vss	ı		5()		10	Between Sections (measured on any channel)		10		IVITIZ
Cin a Ways Distantian				2(*)		5			0.3		
Sine Wave Distortion f _{IS} = 1KHz Sine Wave	$=V_{SS}$	10	1	3(*)		10			0.2		%
IIS - ITAIL OILIC WAVE				5(*)		15			0.12		
CONTROL (Address	or Inhibi	t)				•	•				
Propagation Delay:	0				0	5			360	720	
Address to Signal	0				0	10			160	320	
OUT (Channels ON or OFF)	0				0	15			120	240	ns
or off)	-5				0	5			225	450	
Propagation Delay:	0				0	5			360	720	
Inhibit to Signal OUT	0	1			0	10			160	320	
(Channel turning ON)	0	1			0	15			120	240	ns
	-10				0	5			200	400	
Propagation Delay:	0					5			200	450	
Inhibit to Signal OUT	0	10				10]		90	210	
(Channel turning OFF)	0	10				15			70	160	ns
	-10					5			130	300	
Address or Inhibit to Signal Crosstalk	0	10 ⁽¹⁾			0	10	$V_C = V_{DD} - V_{SS}$ (square wave)		65		mV peak

⁽¹⁾ Both ends of channel.

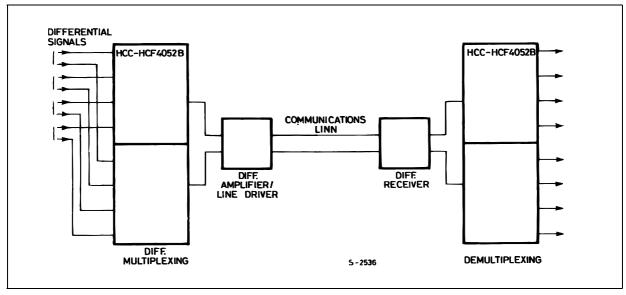
* Peak to Peak voltage symmetrical about (V_{DD} - V_{EE}) /2

TYPICAL BIAS VOLTAGES



The ADDRESS (digital-control inputs) and INHIBIT logic levels are : "0"= V_{SS} and "1"= V_{DD} . The analog signal (through the TG) may swing from V_{EE} to V_{DD}

TYPICAL APPLICATIONS (TYPICAL TIME-DIVISION APPLICATION)

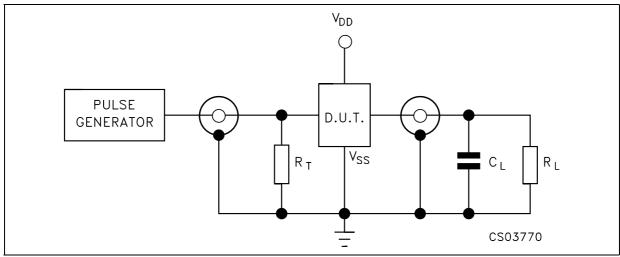


SPECIAL CONSIDERATIONS

Control of analog signals up to 20V peak to peak can be achieved by digital signal amplitudes of 4.5 to 20V (if V_{DD} - V_{SS} = 3V, a V_{DD} - V_{EE} of up to 13V can be controlled; for V_{DD} - V_{EE} level differences above 13V, a V_{DD} - V_{SS} of at least 4.5V is required. For example, if V_{DD} = +5, V_{SS} = 0, and V_{EE} = -13.5, analog signals from -13.5V to 4.5V can be controlled by digital inputs of 0 to 4.5V. In certain applications, the external load resistor

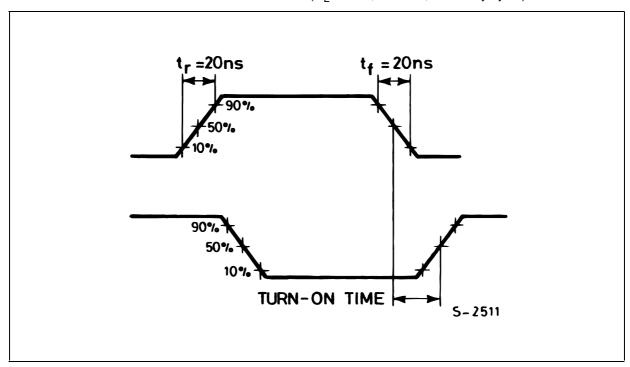
current may include both V_{DD} and signal-line components. To avoid drawing V_{DD} current when switch current flows into the transmission gate inputs, the voltage drop across the bidirectional switch must not exceed 0,8V (calculated from R_{ON} values shown in DC SPECIFICATIONS). No V_{DD} current will flow through R_{L} if the switch current flows into leads 3 and 13.

TEST CIRCUIT

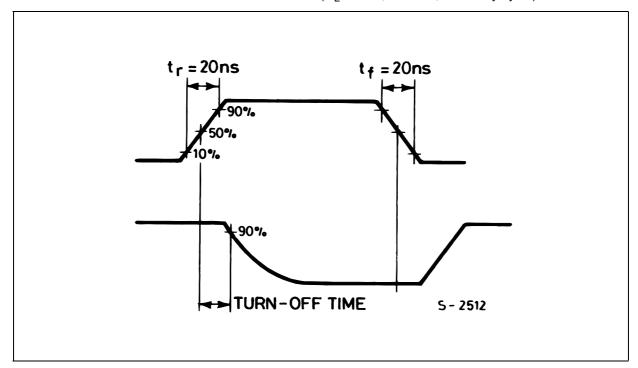


 C_L = 50pF or equivalent (includes jig and probe capacitance) R_L = 200KΩ R_T = Z_{OUT} of pulse generator (typically 50Ω)

WAVEFORM 1 : CHANNEL BEING TURNED ON (R_L = 1K Ω , f=1MHz; 50% duty cycle)

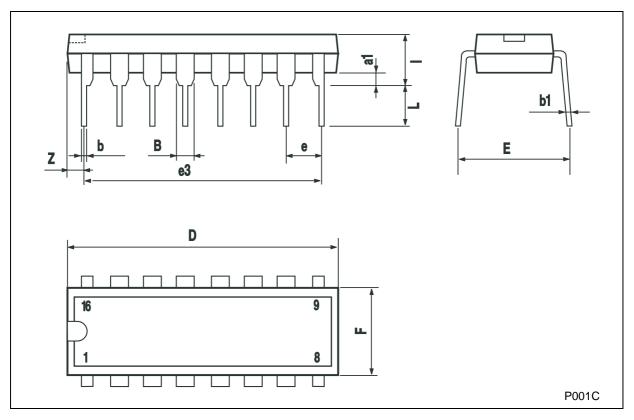


WAVEFORM 2 : CHANNEL BEING TURNED OFF (R_L = 1K Ω , f=1MHz; 50% duty cycle)



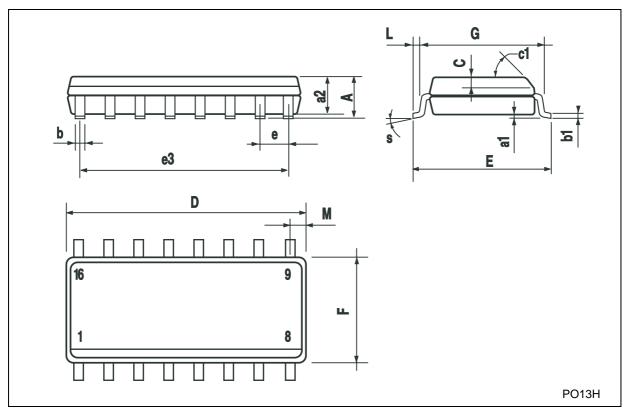
Plastic DIP-16 (0.25) MECHANICAL DATA

DIM		mm.		inch				
DIM.	MIN.	TYP	MAX.	MIN.	TYP.	MAX.		
a1	0.51			0.020				
В	0.77		1.65	0.030		0.065		
b		0.5			0.020			
b1		0.25			0.010			
D			20			0.787		
Е		8.5			0.335			
е		2.54			0.100			
e3		17.78			0.700			
F			7.1			0.280		
I			5.1			0.201		
L		3.3			0.130			
Z			1.27			0.050		



SO-16 MECHANICAL DATA

DIM.		mm.		inch				
DIIVI.	MIN.	TYP	MAX.	MIN.	TYP.	MAX.		
Α			1.75			0.068		
a1	0.1		0.2	0.003		0.007		
a2			1.65			0.064		
b	0.35		0.46	0.013		0.018		
b1	0.19		0.25 0.007			0.010		
С		0.5			0.019			
c1			45°	(typ.)				
D	9.8		10	0.385		0.393		
E	5.8		6.2	0.228		0.244		
е		1.27			0.050			
еЗ		8.89			0.350			
F	3.8		4.0	0.149		0.157		
G	4.6		5.3	0.181		0.208		
L	0.5		1.27	0.019		0.050		
М			0.62			0.024		
S		•	8° (1	max.)		•		



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